

Highly active and porous single-crystal In_2O_3 nanosheet for excellent-response NO_x gas sensor at room temperature

Li Sun,^{a,b} Wencheng Fang,^a Ying Yang,^{a*} Hui Yu,^a Tingting Wang^a, Xiangting Dong,^{a*} Guixia Liu,^a Jinxian Wang,^a Wensheng Yu,^a Keying Shi^{c*}

^a Key Laboratory of Applied Chemistry and Nanotechnology at Universities of Jilin Province, Changchun University of Science and Technology, Changchun 130022

E-mail address: yangying0807@126.com (Y. Yang); dongxiangting888@163.com (X. T. Dong); Fax: +86 0431 85383815; Tel: +86 0431 85582574.

^b College of Chemistry and Chemical Engineering, Qiqihar University, Qiqihar 161006, P. R.

^c Key Laboratory of Functional Inorganic Material Chemistry, Ministry of Education, Heilongjiang University, Harbin 150080, P. R. shikeying2008@163.com (K. Y. Shi);

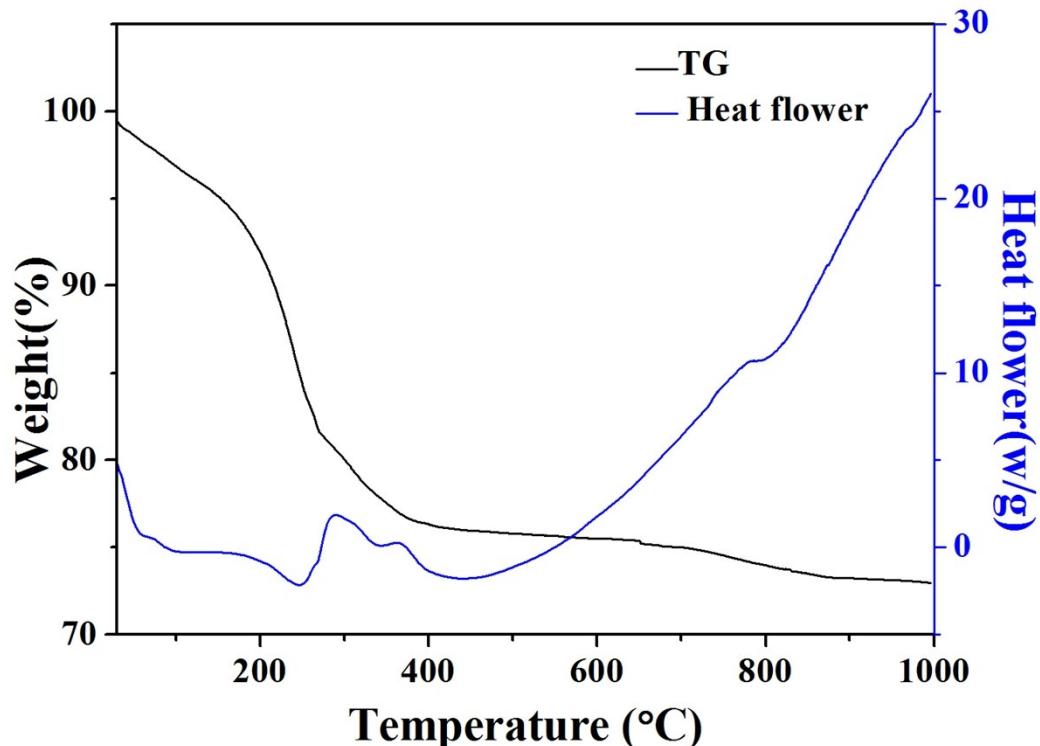


Figure S1. TG-DSC analyses of $\text{In}(\text{OH})_3$ precursors

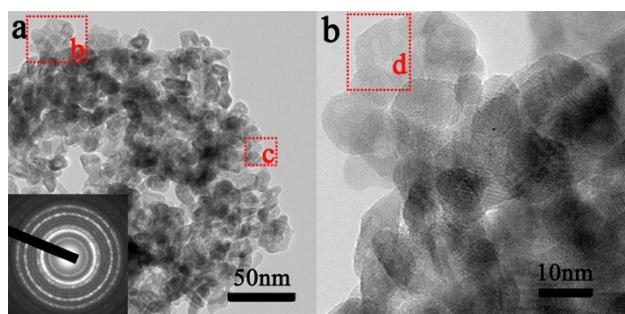


Figure S2. The TEM images of the synthesized In_2O_3 with $0.6 \text{ g } \text{In}(\text{NO}_3)_3$.

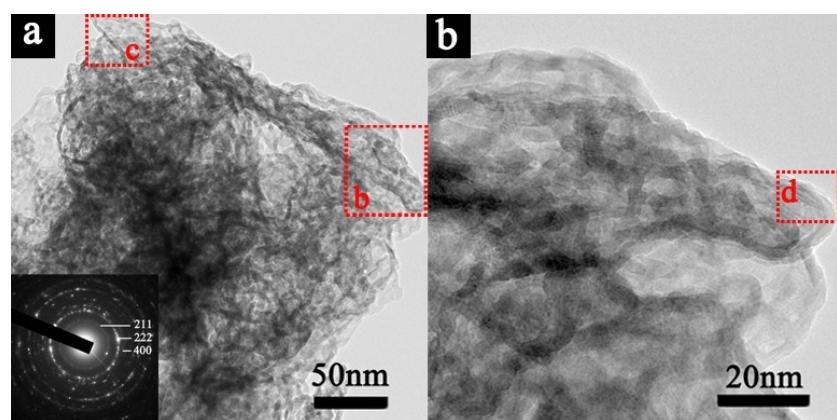


Figure S3. The TEM images of the synthesized In_2O_3 with $0.8 \text{ g } \text{In}(\text{NO}_3)_3$.

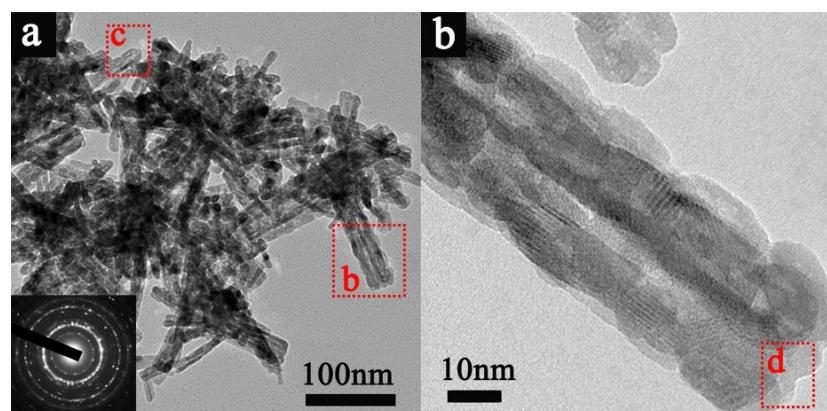


Figure S4. The TEM images of the synthesized In_2O_3 with $1.2 \text{ g } \text{In}(\text{NO}_3)_3$.

Table S1 The results of the surface area, pore volume and pore size.

Sample	S_{BET} ($\text{m}^2 \text{ g}^{-1}$)	pore volume ($\text{cm}^3 \text{ g}^{-1}$)	pore size (nm)
$\text{In}_2\text{O}_3\text{-}0.6$	50.99	0.53	34.73
$\text{In}_2\text{O}_3\text{-}0.7$	52.89	0.47	36.10
$\text{In}_2\text{O}_3\text{-}0.8$	65.70	0.27	18.07
$\text{In}_2\text{O}_3\text{-}0.9$	44.85	0.28	25.51
$\text{In}_2\text{O}_3\text{-}1.0$	41.09	0.29	28.89
$\text{In}_2\text{O}_3\text{-}1.2$	36.33	0.16	21.21

Table S2 The gas response of synthesized In_2O_3 with different $\text{In}(\text{NO}_3)_3$ addition for $97.0 \text{ ppm} \sim 0.485 \text{ ppm NO}_x$ at room temperature.

Sample	Response $(R_N - R_0)/R_0$						
	97.0	48.5 ppm	29.1 ppm	9.70	4.85 ppm	0.97	0.485 ppm
	ppm	ppm	ppm	ppm	ppm	ppm	ppm
$\text{In}_2\text{O}_3\text{-}0.7$	14.45	13.10	9.15	11.49	4.21	2.52	2.46
$\text{In}_2\text{O}_3\text{-}0.8$	20.37	13.48	8.42	3.5	2.24	0.77	--
$\text{In}_2\text{O}_3\text{-}0.9$	89.48	80.26	75.12	45.49	22.72	11.98	4.77
$\text{In}_2\text{O}_3\text{-}1.0$	14.88	13.59	11.62	12.17	8.86	7.95	1.67
$\text{In}_2\text{O}_3\text{-}1.2$	17.00	9.99	7.36	5.39	5.06	2.15	1.73

Table S3 The response time of synthesized In_2O_3 with different $\text{In}(\text{NO}_3)_3$ addition for 97.0 ppm~0.485 ppm NO_x at room temperature.

Sample	Response time (s)						
	97.0	48.5 ppm	29.1 ppm	9.70	4.85 ppm	0.97	0.485 ppm
	ppm			ppm		ppm	
$\text{In}_2\text{O}_3\text{-}0.7$	27	74	182	292	27	182	230
$\text{In}_2\text{O}_3\text{-}0.8$	20.6	20.6	16.6	20.0	27.3	27.3	--
$\text{In}_2\text{O}_3\text{-}0.9$	16.6	24.0	27.3	36.0	38.6	39.3	59.3
$\text{In}_2\text{O}_3\text{-}1.0$	11.33	74.0	79.3	72.6	133	136	400
$\text{In}_2\text{O}_3\text{-}1.2$	17.3	422.0	470.0	492.6	320.0	130.0	203.3

Table S4 The gas sensing performance of In_2O_3 sensors to NO_x gas.

	Material	Operating temperature	NO_x Concentration (ppm)	Response	Lowest detectable limit (ppm)
Our work	ps- In_2O_3 NS	Room temperature	0.485	4.77 ^a	0.485
[S1]	Zn-doped In_2O_3	300 °C	5	2.74 ^b	5
[S2]	Pd-loaded In_2O_3	110 °C	5	9 ^b	5
[S3]	Porous In_2O_3	250 °C	50	164 ^b	1
[S4]	In_2O_3	150 °C	100	33.45 ^b	5
[S5]	In_2O_3 -rGO	Room temperature	30	8.25 ^b	----

^aResponse = $(R_g - R_a)/R_a$; ^bResponse = R_g/R_a , where R_g and R_a are the resistance values of the sensor measured in the target gas and air, respectively.

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